

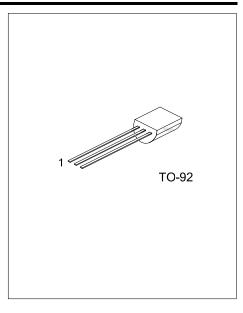
MJE13001-P

NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTOR

FEATURES

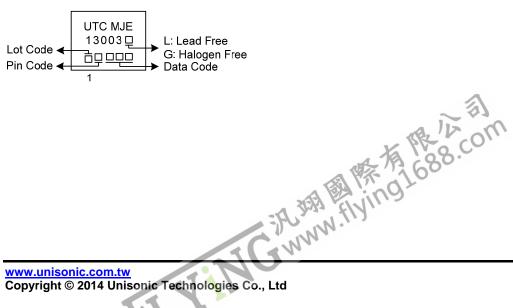
- * Collector-base voltage: V(BR)CBO=600V
- * Collector current: I_C=0.2A



ORDERING INFORMATION

Ordering	Daakaga	Pin	Assignm	Deaking			
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13001L-P-x-T92-A-B	MJE13001G-P-x-T92-A-B	TO-92	Е	С	В	Tape Box	
MJE13001L-P-x-T92-A-K	MJE13001G-P-x-T92-A-K	TO-92	Е	С	В	Bulk	
MJE13001L-P-x-T92-F-B	MJE13001G-P-x-T92-F-B	TO-92	В	С	Е	Tape Box	
MJE13001L-P-x-T92-F-K	MJE13001G-P-x-T92-F-K	TO-92	В	С	E	Bulk	

MARKING



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	V _{CEO}	400	V
Collector-Base Voltage	V _{CBO}	600	V
Emitter Base Voltage	V _{EBO}	7	V
Collector Current	Ι _C	200	mA
Collector Power Dissipation	Pc	750	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100 μA, I _E =0	600			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_{C}=1mA$, $I_{B}=0$	400			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =100 μA, I _C =0	7			V
Base-Emitter Voltage	V _{BE}	I _E =100 mA			1.1	V
Collector Cutoff Cut-Off Current	I _{CBO}	V _{CB} =600V,I _E =0A			100	μA
Collector Emitter Cut-Off Current	I _{CEO}	V _{CE} =400V, I _B =0	0			μA
Emitter Cutoff Cut-Off Current	I _{EBO}	V _{EB} =7V, I _C =0A			100	μA
ON CHARACTERISTICS						
DC Current Gain	h _{FE1} *	V _{CE} =20 V, I _C =20mA	10		70	
	h _{FE2}	V _{CE} =10V, I _C =0.25mA	5			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =50mA, I _B =10mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =50mA, I _B =10mA			1.2	V
SMALL-SIGNAL CHARACTERISTICS						
Current Gain Bandwidth Product	f⊤	c=20mA,V _{CE} =20V,f=1MHz 8				MHz
Resistive Load						
Storage Time	ts	I _C =50mA, I _{B1} =-I _{B2} =5mA,			1.5	μs
Fall Time	t _F	V _{CC} =45V			0.3	μs

■ CLASSIFICATION OF h_{FE1}*

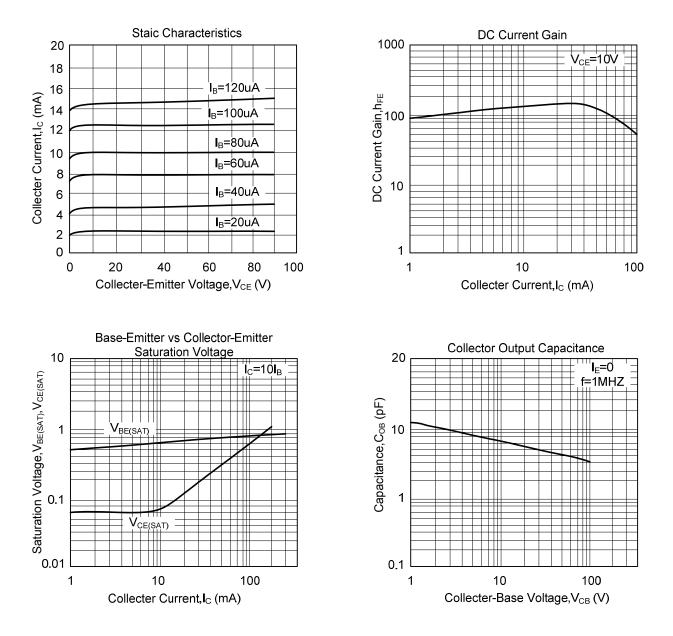
RANK	А	В	С	D	E	F	G	Н	I	J	K	L
RANGE	10-15	15-20	20-25	25-30	30-35	35-40	40-45	45-50	50-55	55-60	60-65	65-70

UNISONIC TECHINOLOGIES CO., LTD

MJE13001-P

NPN SILICON TRANSISTOR

TYPICAL CHARACTERISTICS



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